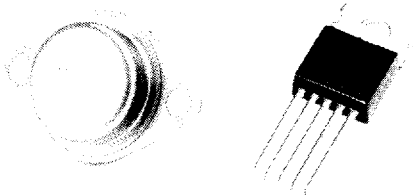


LAS-8100

3 AMP PEAK SWITCHING TRANSISTOR DRIVERS



FEATURES

- Provides simple turn-on and turn-off
- Driver for bipolar and power FETS
- CMOS, NMOS & TTL compatible
- Baker clamp output
- Under voltage lockout

DESCRIPTION

The LAS 8100 Series switching transistor drivers are designed to drive low gain, high current, switching transistors, Darlingtons or FETs at their maximum switching speeds. This is accomplished by providing optimum turn-on (I_{B1}) and turn-off (I_{B2}) drive.

The LAS 8100 monolithic integrated circuit uses non-saturating high speed logic. The input is a Schmidt trigger with 100mV hysteresis providing noise immunity, and can accept a slow rise time. The output is jitter free. The output switching speed is virtually independent of the input switching speed. Under-voltage lockout assures proper operation during power-up and power-down. The output is designed to use the Baker Clamp for non-saturating high speed switching. The push-pull output stage is capable of sourcing and sinking up to 3 amperes.

The LAS 8100 is a single monolithic driver for switching transistors; it is packaged in a hermetically sealed 4 pin TO-3 configuration. The LAS 8101 contains two

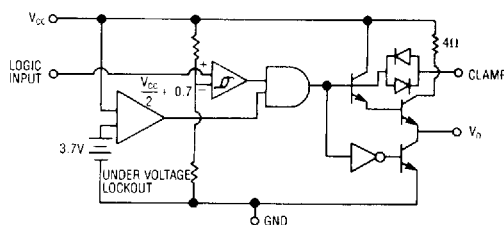
ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | MAXIMUM | UNITS |
|--|--------------------|------------|------------------|
| Supply Voltage | V_{CC} | 26 | Volts |
| Logic Input Voltage | V_{IN} | V_{CC} | Volts |
| Output Current | I_O | 3 | Amps |
| Source (peak) | | 3 | |
| Source (continuous) | | 1 | |
| Sink (peak and continuous) | | 3 | |
| Power Dissipation | P_D | 15 | Watts |
| Thermal Resistance Junction to Case | θ_{JC} | | $^{\circ}C/Watt$ |
| LAS 8100 | | 3 | |
| LAS 8101 | | 2 | |
| LAS 8100P | | 4 | |
| Operating Junction Temperature and Storage Temperature Range | T_J T_{STG} | | $^{\circ}C$ |
| LAS 8100, 8101 | | -55 to 125 | |
| LAS 8100P | | -25 to 125 | |
| Lead Temperature | T_{LEAD} | | $^{\circ}C$ |
| LAS 8100, 8101 (Soldering, 60 seconds) | | 300 | |
| LAS 8100P (Soldering, 10 seconds) | | 260 | |

DEVICE SELECTION GUIDE

| DEVICE | PACKAGE | OUTPUT |
|-----------|---------|--------|
| LAS 8100 | TO-3 | SINGLE |
| LAS 8100P | TO-220 | SINGLE |
| LAS 8101 | TO-3 | DUAL |

BLOCK DIAGRAM



monolithic die to drive two switching devices for double ended converters and other drives. The LAS 8100P is a single monolithic driver packaged in a special TO-220 plastic package.

3 AMP PEAK SWITCHING TRANSISTOR DRIVERS

LAS-8100

ELECTRICAL CHARACTERISTICS

Test conditions are as follows: $V_{CC} = 15V$, $I_O = 0A$, $T_J = 25^\circ C$

| Parameter | Symbol | Test Limits | | | Units |
|---|--------|-------------|---------------|----------------|--------------|
| | | Minimum | Typical | Maximum | |
| Logic Input Threshold | V_T | 7.8 | | 8.6 | Volts |
| Under Voltage Lockout | | 3.5 | | 3.9 | Volts |
| Temperature Coefficient Logic Input Threshold Under Voltage Lockout | T_C | | 0.002 0.01 | 0.003 0.015 | $V/^\circ C$ |
| Logic Input Current | | 10 | 30 | 100 | μA |
| Quiescent Current | I_Q | 10 | 15 | 25 | mA |
| Baker Clamp Source Current | | 3.0 | 4.5 | 7.5 | mA |
| SWITCHING CHARACTERISTICS¹ | | | | | |
| Turn On Delay Time | t_d | | 300 | 500 | ns |
| Rise Time | t_r | | 200 | 300 | ns |
| Turn Off Delay Time | t_s | | 100 | 150 | ns |
| Fall Time | t_f | | 100 | 150 | ns |

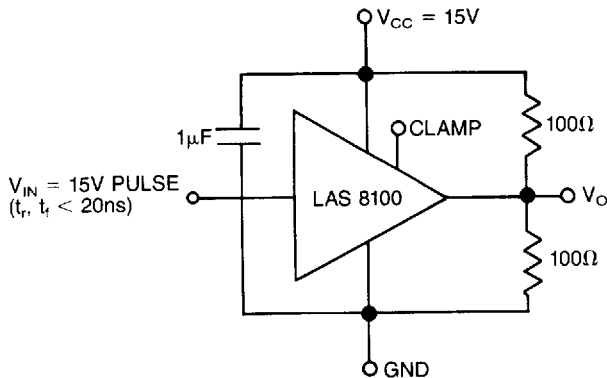
¹ See test circuit.

LAS-8100

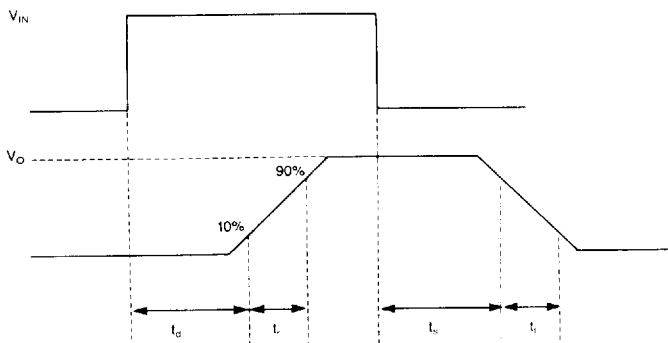
3 AMP PEAK SWITCHING TRANSISTOR DRIVERS

OPERATIONAL DATA

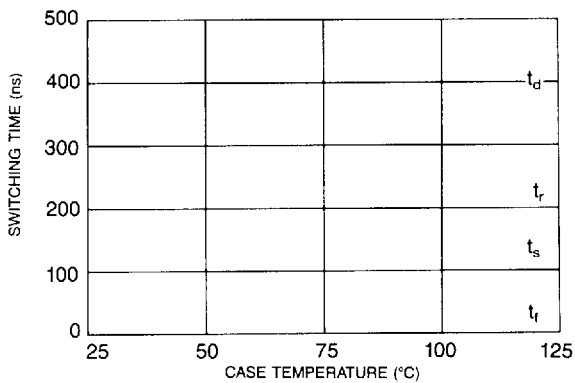
SWITCHING CHARACTERISTICS TEST CIRCUIT



SWITCHING TIMES



SWITCHING TIME VS. CASE TEMPERATURE



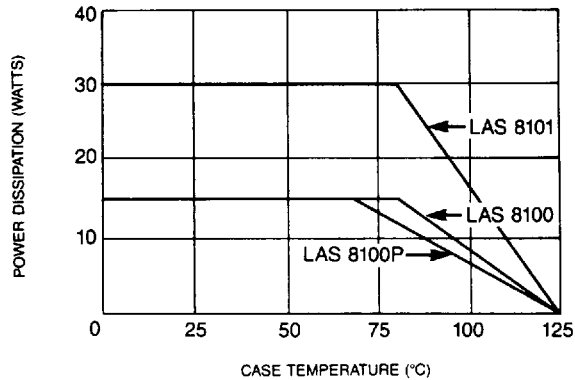
14

3 AMP PEAK SWITCHING TRANSISTOR DRIVERS

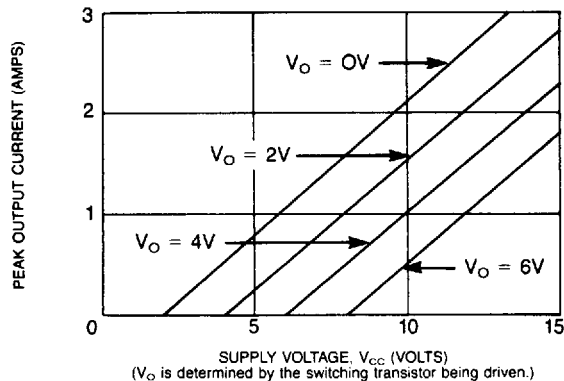
LAS-8100

OPERATIONAL DATA

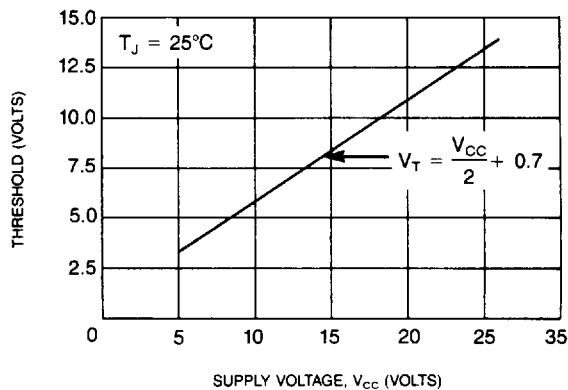
POWER DERATING



PEAK OUTPUT CURRENT VS. SUPPLY VOLTAGE



INPUT LOGIC THRESHOLD



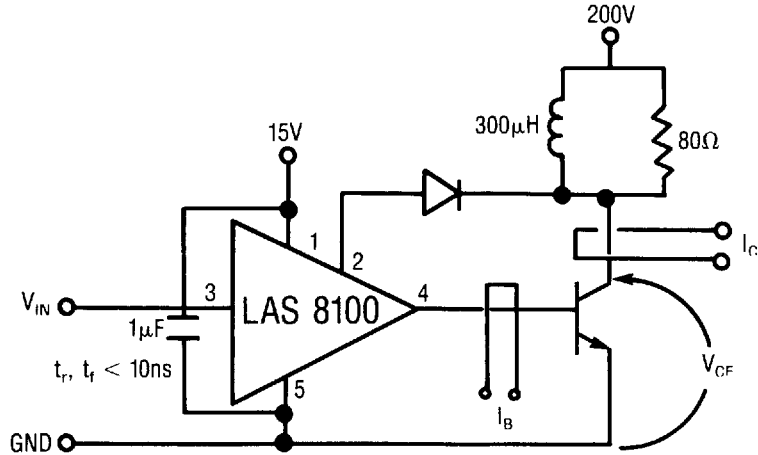
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LAS-8100

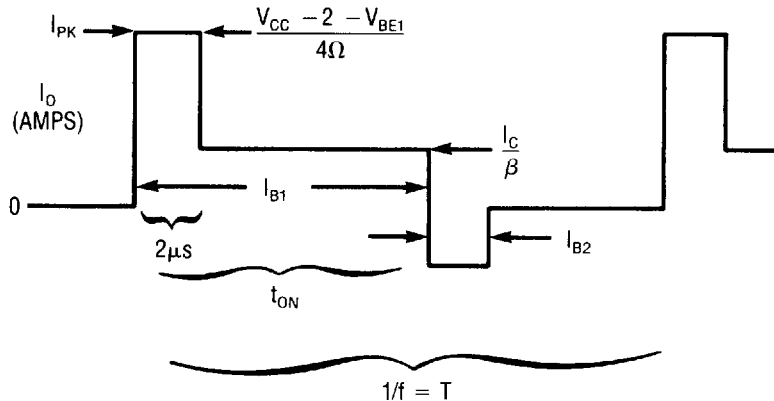
3 AMP PEAK SWITCHING TRANSISTOR DRIVERS

TYPICAL APPLICATION

TRANSISTOR DRIVER



LAS 8100 OUTPUT CURRENT



LAS 8100 AVERAGE POWER DISSIPATION

P_D (avg) = Energy of initial 2 μ s current pulse + Energy of DC current needed to drive transistor switch

$$= f \left\{ \left(\frac{V_{CC} - 2 - V_{BE1}}{4\Omega} \right) (V_{CC} - V_{BE1}) (2\mu s) + \frac{I_C}{\beta} (V_{CC} - V_{BE2}) \left[(\text{d.c.}) (T) - 2\mu s \right] \right\},$$

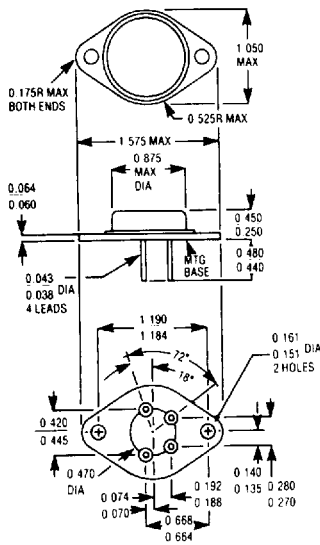
where V_{BE1} = base voltage of switch at turn-on
 V_{BE2} = base voltage of switch at steady state
 d.c. = $\frac{t_{on}}{T}$, duty cycle

3 AMP PEAK SWITCHING TRANSISTOR DRIVERS

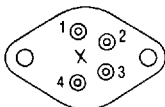
LAS-8100

DEVICE OUTLINE

LAS 8100

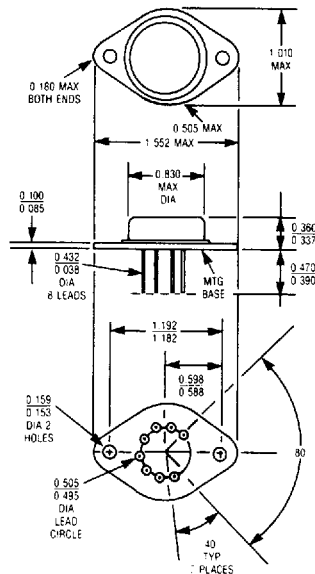


Bottom View

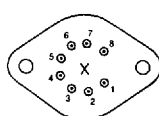


- 1 - V_{CC}
- 2 - Clamp
- 3 - Logic Input
- 4 - Output
- Case is Ground

LAS 8101



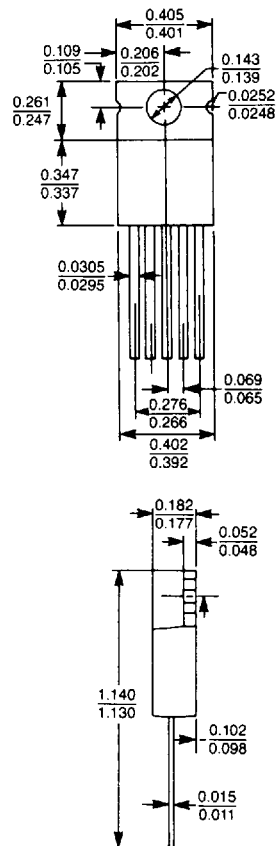
Bottom View



- 1 - Output 1
- 2 - V_{CC} 1
- 3 - Clamp 1
- 4 - Logic Input 1
- 5 - Output 2
- 6 - V_{CC} 2
- 7 - Clamp 2
- 8 - Logic Input 2
- Case is Ground 1, 2

LAS 8100P

(Front View)



- 1 - V_{CC}
- 2 - Clamp
- 3 - Ground
- 4 - Logic Input
- 5 - Output
- Tab is Ground

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NOTE: All dimensions are in inches.